

NPX2 NovaSensor RTPM Sensor



The NPX2 sensor represents the next-generation if remote tire pressure monitoring (RTPM).

The NPX2 sensor includes a pressure sensor, motion detector, an 8-bit RISC processor and a LF input stage to meet demands for a solution that is flexible and reduces overall system cost.

This programmable version of the sensor is available for development and production, there by allowing customers to download their application code and verify the robustness of their software. In order to ensure reliability, the measurement routines for pressure, temperature, acceleration and supply voltage are implemented in ROM.

Features

- Standard pressure ranges: 450, 700 and 1400 kPa
- Single packaged pressure sensor, ASIC and motion detector
- Low power consumption
- Six LSB pressure accuracy 0 to 50 C
- 2.1 to 3.6 volt operation
- 10x overpressure



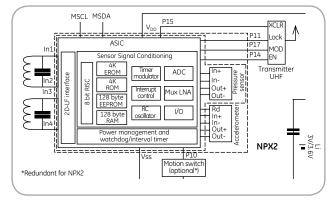
This data sheet contains the overall specifications for the NPX2 family of RTPM sensors. The NPX2 adds the level of integration by including a micro-controller (μ C) and a LF-input stage to meet market demands for flexible, customer specific solutions and overall system cost reduction.

The programmable version of the NPX is available for development and production purposes, that allows the user to download the μ C program in an electrically programmable ROM (E-ROM version). This sensor is intended for developing the application program before migrating in order to ensure high reliability, the production version of the sensor will have the application program implemented in a mask ROM (M-ROM version).

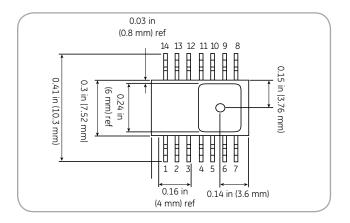
Library Functions

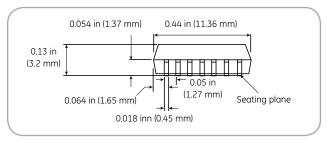
The NPX sensor is designed for RTPM applications. It consists of a RISC core with a number of peripherals. In a supplier-designed part of the firmware memory, implemented library function will include:

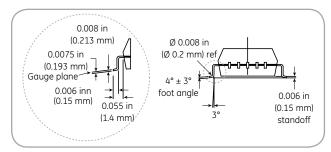
- Measure and compensate acceleration
- Measure and compensate pressure
- Measure and compensate temperature
- Measure and compensate battery voltage The NPX2 device with accelerometer consists of



NPX2 functional diagram







NPX2 top ported dimensions

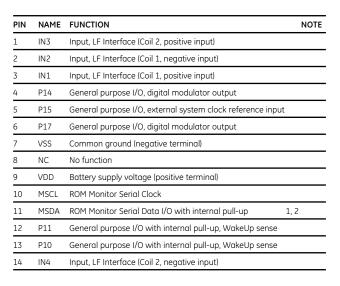
PIN	NAME	FUNCTION	NOTE
1	IN4	Input, LF interface (coil 2, negative input)	
2	P10	General purpose I/O with internal pull-up, wake-up sense	
3	P11	General purpose I/O with internal pull-up, wake-up sense	
4	MSDA	ROM Monitor Serial Data I/O with internal pull-up	1, 2
5	MSCL	ROM Monitor Serial Clock	
6	VDD	Battery supply voltage (positive terminal)	
7	NC	No function	
8	VSS	Common ground (negative terminal)	
9	P17	General purpose I/O or digital modulator output	
10	P15	General purpose I/O or external system clock reference input	
11	P14	General purpose I/O or digital modulator output	
12	IN1	Input, LF interface (coil 1, positive input)	
13	IN2	Input, LF interface (coil 1, negative input)	
14	IN3	Input, LF interface (coil 2, positive input)	

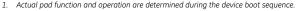
- 1. Actual pad function and operation are determined during the device boot sequence.
- MSCL is an output and must be left unconnected in the application. MSDA feature and on-chip p'up and VBAT may be left open or terminated to VBAT in the application. For field use, the device shall be configured for protected mode, after having flashed the application code, pressure sensor.

three chips: a piezoresistive absolute pressure sensor, a piezoresistive accelerometer, and a CMOS based ASIC, assembled in a standard surface-mount SOIC 14L package. The ASIC is powered by a low power 8-bit RISC processor, performing signal conditioning and data framing according to the application needs. A number of general purpose I/O's are provided to sense and control external circuitry, like a UHF transmitter or additional sensor circuitry. The device incorporates the following features:

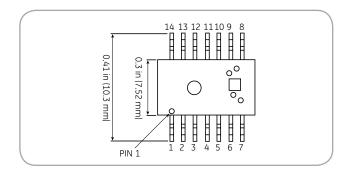
- 2D wake-up LF interface
- Front-end low noise amplifier (LNA)
- ADC configurable from 5 to 12 bits
- Temperature sensor
- Battery voltage detection
- 4 Kbyte ROM
- 4 Kbyte flash EROM
- 128 byte EEPROM
- 128 byte RAM

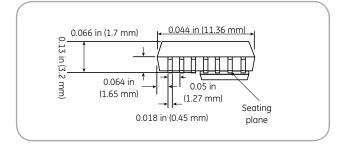
The device employs digital sensor signal compensation with the calibration coefficients stored in EEPROM. The device is in run mode only when demanded by the system, in order to maximize the battery life, returning to either a power down or idle mode. The device can be activated using the integrated accelerometer wake-up to begin execution of the data acquisition routine.

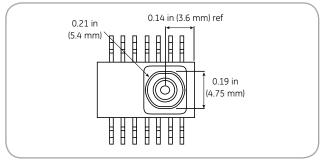


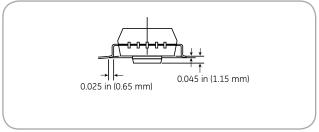


MSCL is an output and must be left unconnected in the application. MSDA feature and on-chip p'up and VBAT may be left open or terminated to VBAT in the application. For field use, the device shall be configured for protected mode, after having flashed the application code, pressure sensor.









NPX2 bottom ported dimensions

Pressure Sensor

The pressure sensor consists of a bulk micro-machined single crystal silicon membrane with an integrated full wheatstone piezoresistive bridge. The pressure sensor contains an absolute pressure reference cavity within the silicon structure. The piezoresistors are placed on the top of the membrane, which in turn are protected by use of a dielectric gel coating that provides the active surface in contact with the tire pressure media.

Accelerometer

The accelerometer consists of a single-crystal silicon, bulk micro-machined beam with an integred full wheatstone piezoresistive bridge. The whole beam is placed inside a hermetically sealed chamber (filled with argon) and is therefore well protected from the environment. A diagnostic resistor, Rd, is integrated along the edge of the beam to be used to check the mechanical integrity of the beam.

Temperature Sensor

The temperature sensor is placed on the ASIC and features a proportional T_0 absolute temperature (PTAT) circuit.

Voltage Sensor

The voltage sensor features a circuit that gives out a voltage proportional to the battery voltage. The battery voltage can then be monitored by the ADC, against an on-chip bandgap voltage used as a reference.

Typical Transfer Functions and **Output Data Format**

450 kPa Pressure

 $P_0 = 0.7286 P - 72.8571$

P = Pressure in kPa

 P_0 = 8 bit scaled output pressure

700 kPa Pressure

 $P_0 = 0.4250 P - 42.5$

P = Pressure in kPa

 $P_0 = 8$ bit scaled output pressure

1400 kPa Pressure

 $P_0 = 0.1818 P$

P = Pressure in kPa

 $P_0 = 8$ bit scaled output pressure

Acceleration

 $A_0 = 2 (A + 12)$

A = Acceleration (g)

 $A_0 = 8$ bit scaled output acceleration

Temperature

 $T_0 = T + 50$

T = Temperature in °F (°C)

 $T_0 = 8$ bit scaled output temperature

Battery Voltage

 $V_0 = 92.5926 (4 - V)$

V = Battery voltage in VDC

 $V_0 = 8$ bit scaled output Vbattery

General

Operating Supply Voltage

2.1 to 3.6 V

Supply Current (2 MHz, Instruction Clock)

400 :A

Power-Down Current

0.5:A

EROM, User Application Code

4 Kbyte

ROM, System Code

(Device-Related Firmware, DSSP Routines)

4 Kbyte

RAM

128 byte

Flag Register (Battery-Backed Flag Register)

EEPROM (Chip Calibration Configuration Data)

RISC Operating Speed, as Derived from **On-Chip RC Oscillator**

0.125 to 2.0 MHz

Limiting Values

All values are in accordance with absolute maximum rating system (IEC 134)

Temperature Range

- Operating range: -40°F to 257°F (-40°C to 125°C)
- Survival range^{1,2}: 347°F (175°C)
- Storage range^{1,3}: -67°F to 257°F (-55°C to 125°C)

Voltage at Any I/O Pin and V_{BAT} Pin to Vss⁴

-0.5 to 4.0 V

Voltage at Any I/O Pin to Vss5

-0.5 to V_{BAT} 0.3 V

Peak Input Current for Pin IN1 and IN2

30 mA

Latch-Up Current⁶

100 mA

ESD

Human Body Model⁷: 2 kV

Machine Model⁸: 200 V

Power Dissipation

120 mW

Vibration (10 to 2000 Hz, Three Axis)

152 g

Static Acceleration (±Z axis)

- 1. At temperature above the operating temperature range, only the flag register and thermal shutdown are active.
- 2. Maximum temperature budget: 302°F to 347°F (150°C to 175°C), 3X 10
- 3. Maximum temperature budget: 257°F to 302°F (125°C to 150°C), 24h accumulated.
- 4. Because of the device concept and design, pin IN1 and IN2 may show a higher voltage during normal device operation, caused by a corresponding input signal applied to IN1 and IN2.
- 5. Voltage must not exceed 4.0 V
- 6. According to JEDEC, JESD 17
- 7. According to JEDEC, JESD 22-A114
- 8. According to JEDEC, JESD 22-A115

Operating Conditions

Tamb = -40°F to 257°F (-40°C to 125°C), V_{BAT} = 3.0 V, V_{SS} = 0 V. Unless otherwise specified.

Symbol	Parameter	Condition	Min.	Typical	Max.	Unit
Battery M	1ode (Battery Supp	ly)				
V _{BAT}	Battery supply voltage	Note 1,2	1.8	_	-	V
V _{BAT}	Battery supply voltage		2.1	_	3.6	V
I _{cc}	Supply current, RC oscillator (CSL = 0)	ADC = 0, POEE = 0				
	Run mode @ Tsys = 2 MHz		_	520	700	μΑ
	Run mode @ Tsys = 125 kHz		_	70	90	μΑ
	Idĺe mode		-	35	45	μΑ
Device Ex	ecutes from EROM	1, V _{BAT} = 3.0 V				
I _{cc}	Supply current RC oscillator (CSL = 0	ADC=0, POEE=0				
	Run mode @ Tsys = 2 MHz		-	630	900	μΑ
	Run mode @ Tsys = 125 kHz		-	70	150	μΑ
I _{QQ}	Power down quiescent current	V _{BAT} = 3.6 V, Tamb = -40°F to 140°F	_	0.6	1.0	μΑ
		(-40°C to 60°C) ³ Tamb = 140°F to 257°F (60°C to 125°C)	-	2	15	μΑ
I _{QQ-1DLF}	Power down quiescent current, LF	V _{BAT} = 3.6 V, Tamb = -40°F to 140°F	-	3.5	7.0	μΑ
	Interface Active	(-40°C to 60°C) ³ Tamb = 140°F to 257°F (60°C to 125°C)	-	5	21	μΑ
I _{QQ-2DLF}	Power down quiescent current, LF interface active	V _{BAT} = 3.6 V, Tamb = -40°F to 140°F (-40°C to 60°C) ³	-	4.5	9.0	μА
I _{QQ-SHTD}	Power down quiescent current	V _{BAT} = 3.6 V, Tamb = 257°F (-125°C) ⁴	_	_	30	μΑ

- Some functions or operations are not supported.
 - LNA, measurement of pressure and ambient temperature LF wake-up with reduced performance
- Temperature shut-down active Device timer tick on

Device operation down to VTHR is granted, however, parameters may be out of specification.

Measurement Performance

Four main measurements can be selected: Pressure (P), acceleration (A), temperature (T) and battery voltage (V). This section describes the performance of each measurement.

Pressure Measurement

The present performance reflects the use of 12-bit sampling of pressure signal by using a two-temperature calibration methodology.

Parameter	Specification			Ambient	Ambient Conditions		
	Min	Тур	Max	Unit	Temp	VDD	
Pressure Range							
450 kPa	100		450	kPa	-40°F to 257°F (-40°C to 125°C)	2.1 to 3.6 V	_
700 kPa	100	-	700	kPa	-40°F to 257°F (-40°C to 125°C)	2.1 to 3.6 V	_
1400 kPa	0	-	1402.5	kPa	-40°F to 257°F (-40°C to 125°C)	2.1 to 3.6 V	_
Resolution							
450 kPa	_	1.3789	_	kPa/LSB	-40°F to 257°F (-40°C to 125°C)	2.1 to 3.6 V	_
700 kPa	_	2.3529	_	kPa/LSB	-40°F to 257°F (-40°C to 125°C)	2.1 to 3.6 V	_
1400 kPa	-	5.50	_	kPa/LSB	-40°F to 257°F (-40°C to 125°C)	2.1 to 3.6 V	_
Measurement Accuracy	-6	_	6	LSB	32°F to 122°F (0°C to 50°C)	2.1 to 3.6 V	_
,	-8	_	8	LSB	-40°F to 257°F (-40°C to 125°C)	2.1 to 3.6 V	_
Overpressure	-	10X	-		-	_	-
Measurement	_	3.7	4.2	μC	77°F (25°C)	3.0 V	11-bit sampling
Charge Consumption	_	3.9 3.5	4.5 4.0	μC μC	-40°F (-40°C) 257°F (125°C)	3.0 V 3.0 V	11-bit sampling 11-bit sampling

Measurement accuracy verification performed at 77°F and 257°F (25°C and 125°C) in production test. Capability proved through qualification at < 77°F (< 25°C).

Acceleration Measurement

The present performance reflects the use of 12-bit sampling of pressure signal by using a two-temperature calibration methodology.

Parameter	Specification			Ambient	Ambient Conditions		
	Min	Тур	Max	Unit	Temp	VDD	
Rolling/Stationary Mode Threshold Acceleration	2	_	17	g	-40°F to 257°F (-40°C to 125°C)	2.1 to 3.6 V	-
Input Range	-12		115	g	-40°F to 257°F (-40°C to 125°C)	2.1 to 3.6 V	_
Resolution	-	0.5	-	g/LSB	-40°F to 257°F (-40°C to 125°C)	2.1 to 3.6 V	_
Sensitivity Accuracy	-15	-	15	%	-40°F to 257°F (-40°C to 125°C)	2.1 to 3.6 V	_
Offset Accuracy	-8	-	8	g	-40°F to 257°F (-40°C to 125°C)	2.1 to 3.6 V	_
Measurement Charge Consumption	_ _ _	6.3 6.5 6.1	7.2 7.5 7.0	μC μC μC	77°F (25°C) -40°F (-40°C) 257°F (125°C)	3.0 V 3.0 V 3.0 V	_ _ _

Measurement accuracy verification performed at 77°F and 257°F (25°C and 125°C) in production test. Capability proved through qualification at < 77°F (< 25°C).

Temperature Measurement

The present performance reflects the use of 10-bit sampling of temperature signal.

Parameter	Specification			Ambient	Ambient Conditions		Comments	
	Min	Тур	Max	Unit	Temp	VDD		
Temperature Range	-40°	-	257°	F	_	_	-40°C to 125°C	
Resolution	-	1.0	-	°C/LSB	_	-	401°F - (-58°F)/255 205°C - (-50°C)/255	
Measurement Accuracy	-5 -3	- -	7 3	LSB LSB	-40°F to 257°F -4°F to 158°F	2.1 to 3.6 V 2.1 to 3.6 V	-40°C to 125°C -20°C to 70°C	
Measurement Charge Consumption	_ _ _	1.0 1.1 1.0	1.1 1.2 1.15	μC μC	77°F (25°C) -40°F (-40°C) 257°F (125°C)	3.0 V 3.0 V 3.0 V		

 $Measurement\ accuracy\ verification\ performed\ at\ 77^{\circ}F\ and\ 257^{\circ}F\ (25^{\circ}C\ and\ 125^{\circ}C)\ in\ production\ test.\ Capability\ proved\ through\ qualification\ at\ <\ 77^{\circ}F\ (<\ 25^{\circ}C)\ in\ production\ test.\ Capability\ proved\ through\ qualification\ at\ <\ 77^{\circ}F\ (<\ 25^{\circ}C)\ in\ production\ test.\ Capability\ proved\ through\ qualification\ at\ <\ 77^{\circ}F\ (<\ 25^{\circ}C)\ in\ production\ test.\ Capability\ proved\ through\ qualification\ at\ <\ 77^{\circ}F\ (<\ 25^{\circ}C)\ in\ production\ test.\ Capability\ proved\ through\ qualification\ at\ <\ 77^{\circ}F\ (<\ 25^{\circ}C)\ in\ production\ test.\ Capability\ proved\ through\ qualification\ at\ <\ 77^{\circ}F\ (<\ 25^{\circ}C)\ in\ production\ test.\ Capability\ proved\ through\ qualification\ at\ <\ 77^{\circ}F\ (<\ 25^{\circ}C)\ in\ production\ test.\ Capability\ proved\ through\ qualification\ at\ <\ 77^{\circ}F\ (<\ 25^{\circ}C)\ in\ production\ test.\ Capability\ proved\ through\ qualification\ at\ <\ 77^{\circ}F\ (<\ 25^{\circ}C)\ in\ production\ test.\ Capability\ proved\ through\ qualification\ at\ <\ 77^{\circ}F\ (<\ 25^{\circ}C)\ in\ production\ test.\ Capability\ proved\ through\ qualification\ at\ <\ 77^{\circ}F\ (<\ 25^{\circ}C)\ in\ production\ test.\ Capability\ proved\ through\ qualification\ at\ <\ 77^{\circ}F\ (<\ 25^{\circ}C)\ in\ production\ test.\ Capability\ proved\ through\ qualification\ at\ qualification\ at\ qualification\ qualification$

Battery Voltage Measurement

The present performance reflects the use of 9-bit sampling of battery voltage signal.

Parameter	Specification			Ambient	Ambient Conditions		Comments	
	Min	Тур	Max	Unit	Temp	VDD		
Resolution	-	10.8	-	mV/LSB	-	_	(4.0 -1.246)/255	
Measurement Accuracy	-6	_	6	LSB	-40°F to 257°F (-40°C to 125°C)	2.1 to 3.6 V	-	
Measurement Charge Consumption	_ _ _	0.50 0.55 0.50	0.55 0.6 0.55	μC μC μC	77°F (25°C) -40°F (-40°C) 257°F (125°C)	3.0 V 3.0 V 3.0 V	_ _ _	

 $Measurement\ accuracy\ verification\ performed\ at\ 77^\circ F\ and\ 257^\circ F\ (25^\circ C)\ in\ production\ test.\ Capability\ proved\ through\ qualification\ at\ <\ 77^\circ F\ (<\ 25^\circ C)\ in\ production\ test.\ Capability\ proved\ through\ qualification\ at\ <\ 77^\circ F\ (<\ 25^\circ C)\ in\ production\ test.\ Capability\ proved\ through\ qualification\ at\ <\ 77^\circ F\ (<\ 25^\circ C)\ in\ production\ test.\ Capability\ proved\ through\ qualification\ at\ <\ 77^\circ F\ (<\ 25^\circ C)\ in\ production\ test.\ Capability\ proved\ through\ qualification\ at\ <\ 77^\circ F\ (<\ 25^\circ C)\ in\ production\ test.\ Capability\ proved\ through\ qualification\ at\ <\ 77^\circ F\ (<\ 25^\circ C)\ in\ production\ test.\ Capability\ proved\ through\ qualification\ at\ <\ 77^\circ F\ (<\ 25^\circ C)\ in\ production\ test.\ Capability\ proved\ through\ qualification\ at\ <\ 77^\circ F\ (<\ 25^\circ C)\ in\ production\ test.\ Capability\ proved\ through\ qualification\ at\ <\ 77^\circ F\ (<\ 25^\circ C)\ in\ production\ test.\ Capability\ proved\ through\ qualification\ at\ <\ 77^\circ F\ (<\ 25^\circ C)\ for\ production\ test.\ Capability\ proved\ through\ qualification\ at\ <\ 77^\circ F\ (<\ 25^\circ C)\ for\ production\ test.\ Capability\ proved\ through\ qualification\ at\ <\ 77^\circ F\ (<\ 25^\circ C)\ for\ production\ test.\ Capability\ proved\ through\ qualification\ at\ (<\ 25^\circ C)\ for\ production\ test.\ Capability\ proved\ through\ qualification\ at\ (<\ 25^\circ C)\ for\ production\ test.\ Capability\ proved\ through\ qualification\ through\ qualification\ through\ qualification\ through\ qualification\ qualification\ qualification\ through\ qualification\ qual$

Abbreviation and definitions

The following abbreviations and definitions are used throughout the document:

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ABC	Analog to Digital Converter
ASIC	Application Specific Integrated Circuit
CMOS	Complementary metal oxide semiconductor
EEPROM	Electrically erasable programmable read-only memory
1/0	Input and output
LNA	Low Noise Amplifier
LF	Low Frequency
LSB	Least significant bit
%FS	% referred to range (max - min)
PTAT	Proportional to Absolute Temperature
RISC	Reduced Instruction-Set Computing
ROM	Read Only Memory
RTPM	Remote Tire Pressure Monitoring
SFR	Special Function Register
TBC	To Be Confirmed
TBD	To Be Defined

